

666th ASRC Seminar

Date: Thursday, March 2, 13:30 ~

Location: Room 103, ASRC bldg.

Speaker: Professor Maki Suemitsu
(Tohoku University)

Title: Growth of SiC thin film on Si substrates and formation of epitaxial graphene thereon

Abstract: By use of original gas-source (GS) MBE technique, qualified thin films of 3C-SiC can be grown on Si substrates. By further annealing the 3C-SiC films in vacuum, we can even fabricate epitaxial graphene thereon. The benefit of this “graphene-on-Si” technology lies in its ability in controlling the stacking order, and thus the physical properties, of the epitaxial graphene. The hydrogen-related surface chemistry during GSMBE, as well as the current status of the EG on Si will be reviewed.

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